

## HCT/DDOCESS CHANCE NOTICE (DCN)

PRODUCT/PROC	ESS CHANGE NOTICE (PCN)		
PCN #: SM-0308-02 DATE: 8/ Product Affected: 70121 / 70125 2Kx9 Dual-Port F  Date Effective: 11/15/2003	MEANS OF DISTINGUISHING CHANGED DEVICES:  ■ Product Mark Die revision "R" marked on top  □ Back Mark of the part near the date code  □ Date Code  □ Other		
Contact: Dennis Lantz			
Title: Quality/Reliability Manager Phone #: (831) 775-4032 Fax #: (831) 754-4672	Attachment:: Yes No Samples: Available now		
E-mail: <u>dennis.lantz@idt.com</u>	Contact your IDT Sales Representative		
DESCRIPTION AND PURPOSE OF CHANGE:  □ Die Technology □ Wafer Fabrication Process □ Assembly Process □ Equipment □ Material □ Testing □ Manufacturing Site □ Data Sheet □ Other	To consolidate Wafer Fab production from Salinas, California (Fab 2) to Hillsboro, Oregon (Fab4). These qualified products will be transferred to IDT's Wafer Fab facility in Hillsoboro, Oregon. These devices will be upgraded from Cmos 7 (.64um) to Cmos 8 (.60um). Cmos 8 is an existing qualifed process at Fab 4.		
<b>RELIABILITY/QUALIFICATION SUMMARY:</b> Qualification testing has been completed and verifies the details are attached	nat there is no change to the product reliability. Qualification		
to grant approval or request additional information. If it will be assumed that this change is acceptable.	PT: ion of this change. Please use the acknowledgement below or E-Mail IDT does not receive acknowledgement within 30 days of this notice ured after the process change effective date until the inventory		
Customer:	☐ Approval for shipments prior to effective date.		
Name/Date:	E-Mail Address:		
Title:	Di # /F# .		
CUSTOMER COMMENTS:			
CUSTOMER COMMENTS.			
IDT ACKNOWLEDGMENT OF RECEIPT:			
IDI ACKNOWLEDGIVIENT OF RECEIPT:			
RECD. BY:	DATE:		

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### ATTACHMENT - PCN #: SM-0308-02

**PCN Type:** Fab Site Change

Data Sheet Change None Expected

**Detail of Change** Transfer existing qualified products from Salinas, California Wafer Fab Facility (Fab 2) to Hillsboro,

Oregon Wafer Fab Facility (Fab 4).

	Current Die Revision	Future Die Revision
Die Revision	V	R
Wafer Fab Tech	Cmos 7	Cmos 8
Wafer Size	6 inch	8 inch
# Poly Layers	2	2
# Metal Layers	2	2
Die Dimensions (sq mils)	11.96	10.92

#### **Conversion Schedule (Estimated)**

Base Device Production Shipments and Sample Availability

70121S Now 70125S Now

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### ATTACHMENT - PCN #: SM-0308-02

Qualification Plan: QSM-0304-01

Test Vehicle	Test Results
7132S4	Sample Size/ # of Fails
Operating Life Test: Dynamic @+135°C, Vcc=4V for 750 hours	116 / 0
High Temp. Storage Life Test (Unbiased, 1000 hours @+150°C)	77 / 0
Bake & Ballshear Test @ 200°C / 4 ball bonds per device	5/0
Temperature Cycling: ( -65°C to +150°C, 500 cycles)	45 / 0
HAST: (Biased, 100 Hrs. @+130°C, +85%RH, 3 Atm.)	45 / 0
Autoclave:(Unbiased, 2 Atm Saturated Steam, +121°C, 168 Hrs)	45 / 0
ESD Human Body Model	9/0
ESD Charged Device Model	6/0
Latch up: ( Tested to 2X Vcc)	10 / 0